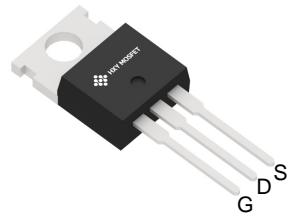




Description

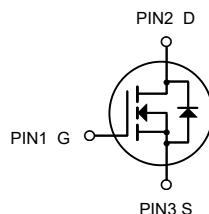
The HXY5N40P can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-220C, which accords with the RoHS standard.



TO-220C

General Features

$V_{DS} = 400V$, $I_D = 5.5A$
 $R_{DS(ON)} < 1 \Omega$ @ $V_{GS}=10V$



N-Channel MOSFET

Application

- Power switch circuit of adaptor and charger.

Ordering Information

Product ID	Pack	Brand	Units Tube
HXY5N40P	TO-220C	HXY MOSFET	50

Absolute Maximum Ratings@T = 25°C(unless otherwise specified)

Symbol	Parameter	Limit	Unit
V_{DSS}	Drain-to-Source Voltage ^[1]	400	V
V_{GSS}	Gate-to-Source Voltage	± 30	
I_D	Continuous Drain Current	5.5	A
I_D @ $T_c = 100^\circ C$	Continuous Drain Current @ $T_c = 100^\circ C$	3.5	
I_{DM}	Pulsed Drain Current at $V_{GS} = 10V$ ^[2]	22	
E_{AS}	Single Pulse Avalanche Energy	290	mJ
T_J & T_{STG}	Operating and Storage Temperature Range	-55 to 150	°C
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.9	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.



Electrical Characteristics $T_J=25^\circ\text{C}$ unless otherwise specified

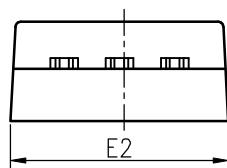
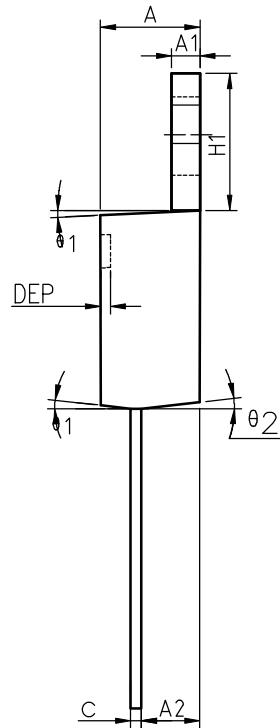
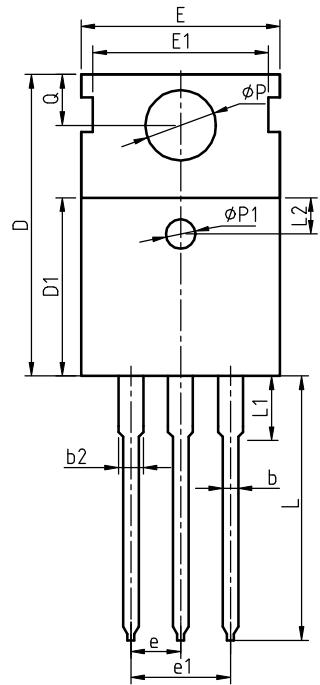
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	400			V
Gate-threshold voltage	$V_{(\text{GS})\text{th}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	2		4	
Gate-body leakage	I_{GSS}	$V_{\text{DS}}=0\text{V}, V_{\text{GS}}=\pm 20\text{V}$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}}=400\text{V}, V_{\text{GS}}=0\text{V}$			25	μA
		$V_{\text{DS}}=320\text{V}, V_{\text{GS}}=0\text{V}, T_J=125^\circ\text{C}$			250	
Drain-source on-resistance (note 4)	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=3.3\text{A}$		0.92	1.0	Ω
Forward transconductance (note 4)	g_{fs}	$V_{\text{DS}}=50\text{V}, I_{\text{D}}=3.3\text{A}$	2.9			S
Diode forward voltage	V_{SD}	$I_{\text{S}}=5.5\text{A}, V_{\text{GS}}=0\text{V}$			1.6	V
Total gate charge	Q_{g}	$V_{\text{DS}}=320\text{V}, V_{\text{GS}}=10\text{V}, I_{\text{D}}=3.5\text{A}$			38	nC
Gate-source charge	Q_{gs}				5.7	
Gate-drain charge	Q_{gd}				22	
Input capacitance (note 5)	C_{iss}	$V_{\text{DS}}=25\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$		700		pF
Output capacitance (note 5)	C_{oss}			170		
Reverse transfer capacitance (note 5)	C_{rss}			64		
Turn-on time(note 4,5)	$t_{\text{d(on)}}$	$V_{\text{DD}}=200\text{V}, R_{\text{D}}=57\Omega, I_{\text{D}}=3.5\text{A}, R_{\text{G}}=12\Omega$		10		ns
Rise time(note 4,5)	t_{r}			15		
Turn-off time(note 4,5)	$t_{\text{d(off)}}$			38		
Fall time(note 4,5)	t_{f}			14		

Notes:

1. Repetitive Rating ;Pulse width limited by maximum junction temperature.
2. $L=16\text{mH}, I_{\text{AS}}=5.5\text{A}, V_{\text{DD}}=50\text{V}, R_{\text{G}}=25\Omega$, starting $T_J=25^\circ\text{C}$.
3. $I_{\text{SD}}\leq 5.5\text{A}$, $di/dt\leq 90\text{A}/\mu\text{s}$, $V_{\text{DD}}\leq V_{(\text{BR})\text{DSS}}$, $T_J\leq 150^\circ\text{C}$.
4. Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.
5. These parameters have no way to verify.



Package Information TO-220C



COMMON DIMENSIONS

SYMBOL	MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185
A1	1.27	1.30	1.33	0.050	0.051	0.052
A2	2.35	2.40	2.50	0.093	0.094	0.098
b	0.77	0.80	0.90	0.030	0.031	0.035
b2	1.17	1.27	1.36	0.046	0.050	0.054
c	0.48	0.50	0.56	0.019	0.020	0.022
D	15.40	15.60	15.80	0.606	0.614	0.622
D1	9.00	9.10	9.20	0.354	0.358	0.362
DEP	0.05	0.10	0.20	0.002	0.004	0.008
E	9.80	10.00	10.20	0.386	0.394	0.402
E1	-	8.70	-	-	0.343	-
E2	9.80	10.00	10.20	0.386	0.394	0.402
e		2.54	BSC		0.100	BSC
e1		5.08	BSC		0.200	BSC
H1	6.40	6.50	6.60	0.252	0.256	0.260
L	12.75	13.50	13.65	0.502	0.531	0.537
L1	-	3.10	3.30	-	0.122	0.130
L2		2.50	REF		0.098	REF
P	3.50	3.60	3.63	0.138	0.142	0.143
P1	3.50	3.60	3.63	0.138	0.142	0.143
Q	2.73	2.80	2.87	0.107	0.110	0.113
θ1	5°	7°	9°	5°	7°	9°
θ2	1°	3°	5°	1°	3°	5°
θ3	1°	3°	5°	1°	3°	5°



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